



August 2000

QFET™

FQP70N08

80V N-Channel MOSFET

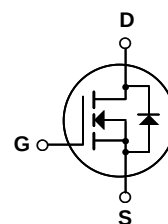
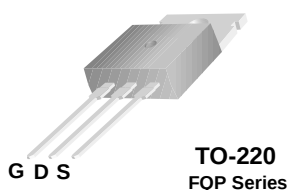
General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as automotive, high efficiency switching for DC/DC converters, and DC motor control.

Features

- 70A, 80V, $R_{DS(on)} = 0.017\Omega$ @ $V_{GS} = 10V$
- Low gate charge (typical 75 nC)
- Low C_{rss} (typical 180 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- 175°C maximum junction temperature rating



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP70N08	Units
V_{DSS}	Drain-Source Voltage	80	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	70	A
		49.5	A
I_{DM}	Drain Current - Pulsed (Note 1)	280	A
V_{GSS}	Gate-Source Voltage	± 25	V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	1150	mJ
I_{AR}	Avalanche Current (Note 1)	70	A
E_{AR}	Repetitive Avalanche Energy (Note 1)	15.5	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	6.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	155	W
		1.03	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +175	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	0.97	°C/W
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink	0.5	--	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	62.5	°C/W

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	80	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C	--	0.08	--	V/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 64\text{ V}, T_C = 150^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 25\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -25\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 35\text{ A}$	--	0.013	0.017	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 30\text{ V}, I_D = 35\text{ A}$ (Note 4)	--	41	--	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	2100	2700	pF
C_{oss}	Output Capacitance		--	790	1030	pF
C_{rss}	Reverse Transfer Capacitance		--	180	230	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 40\text{ V}, I_D = 70\text{ A},$ $R_G = 25\text{ }\Omega$ (Note 4, 5)	--	25	60	ns
t_r	Turn-On Rise Time		--	300	610	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	190	ns
t_f	Turn-Off Fall Time		--	145	300	ns
Q_g	Total Gate Charge	$V_{DS} = 64\text{ V}, I_D = 70\text{ A},$ $V_{GS} = 10\text{ V}$ (Note 4, 5)	--	75	98	nC
Q_{gs}	Gate-Source Charge		--	14	--	nC
Q_{gd}	Gate-Drain Charge		--	37	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	70	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	280	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 70 A	--	--	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 70 A,	--	84	--	ns
Q _{rr}	Reverse Recovery Charge	dI _F / dt = 100 A/μs (Note 4)	--	250	--	nC

Notes:

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. $L = 0.32\text{ mH}, I_{AS} = 70\text{ A}, V_{DD} = 25\text{ V}, R_G = 25\text{ }\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 70\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$
5. Essentially independent of operating temperature

Typical Characteristics

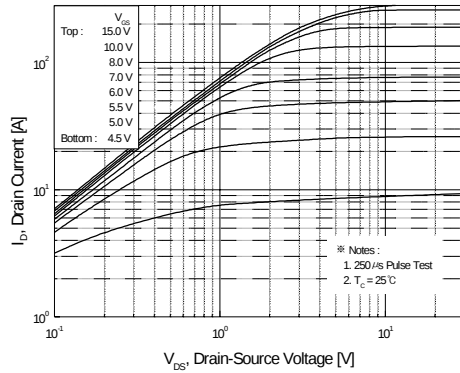


Figure 1. On-Region Characteristics

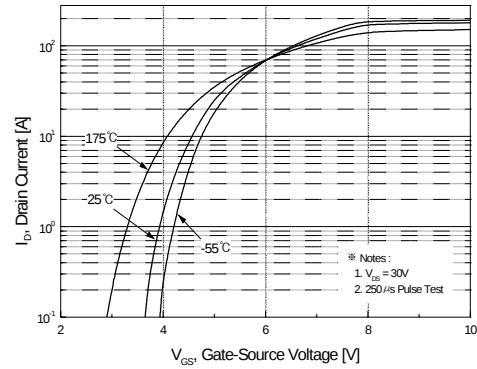


Figure 2. Transfer Characteristics

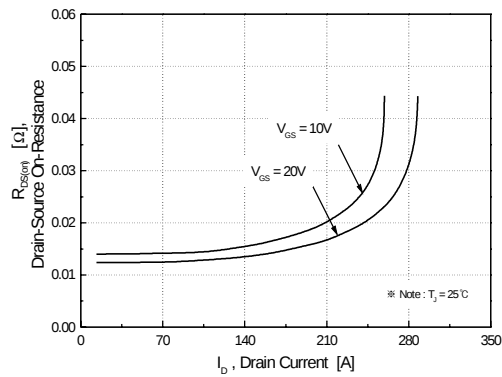


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

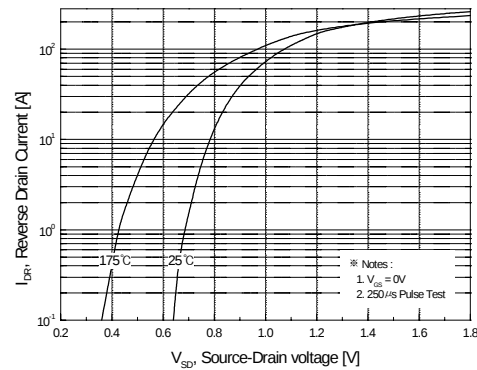


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

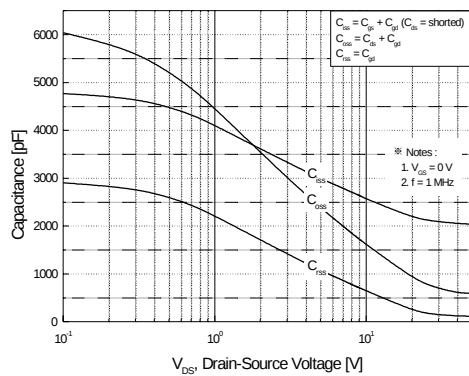


Figure 5. Capacitance Characteristics

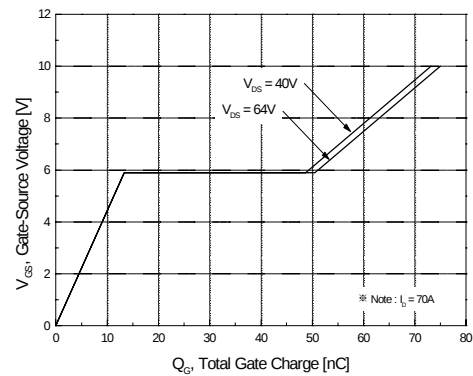


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

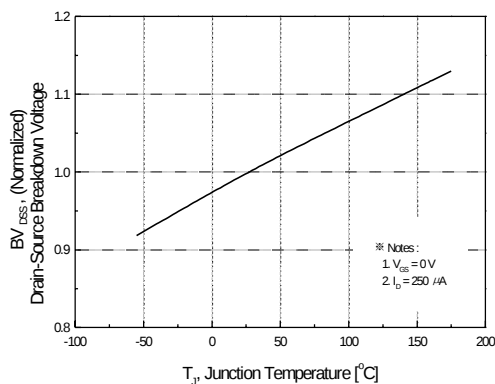


Figure 7. Breakdown Voltage Variation vs. Temperature

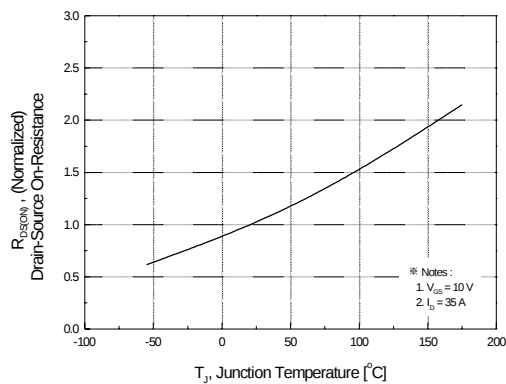


Figure 8. On-Resistance Variation vs. Temperature

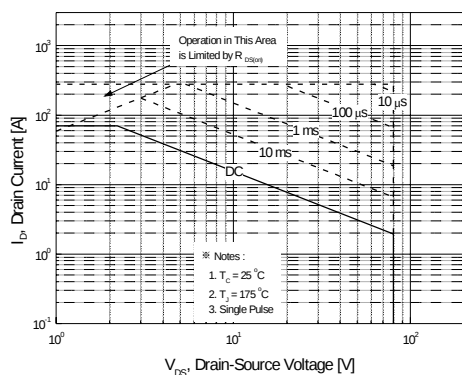


Figure 9. Maximum Safe Operating Area

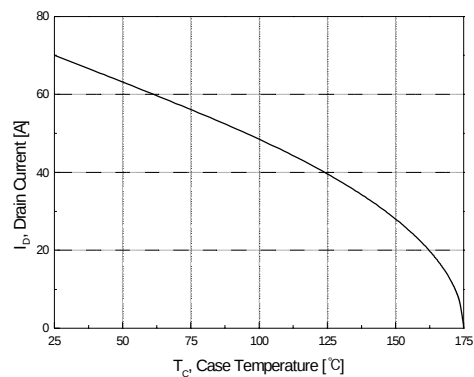


Figure 10. Maximum Drain Current vs. Case Temperature

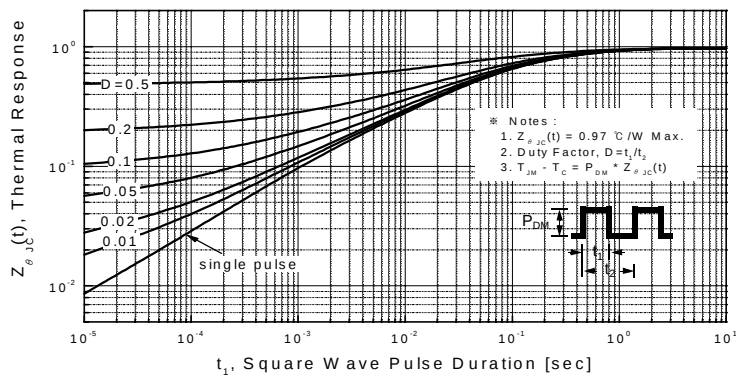


Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform

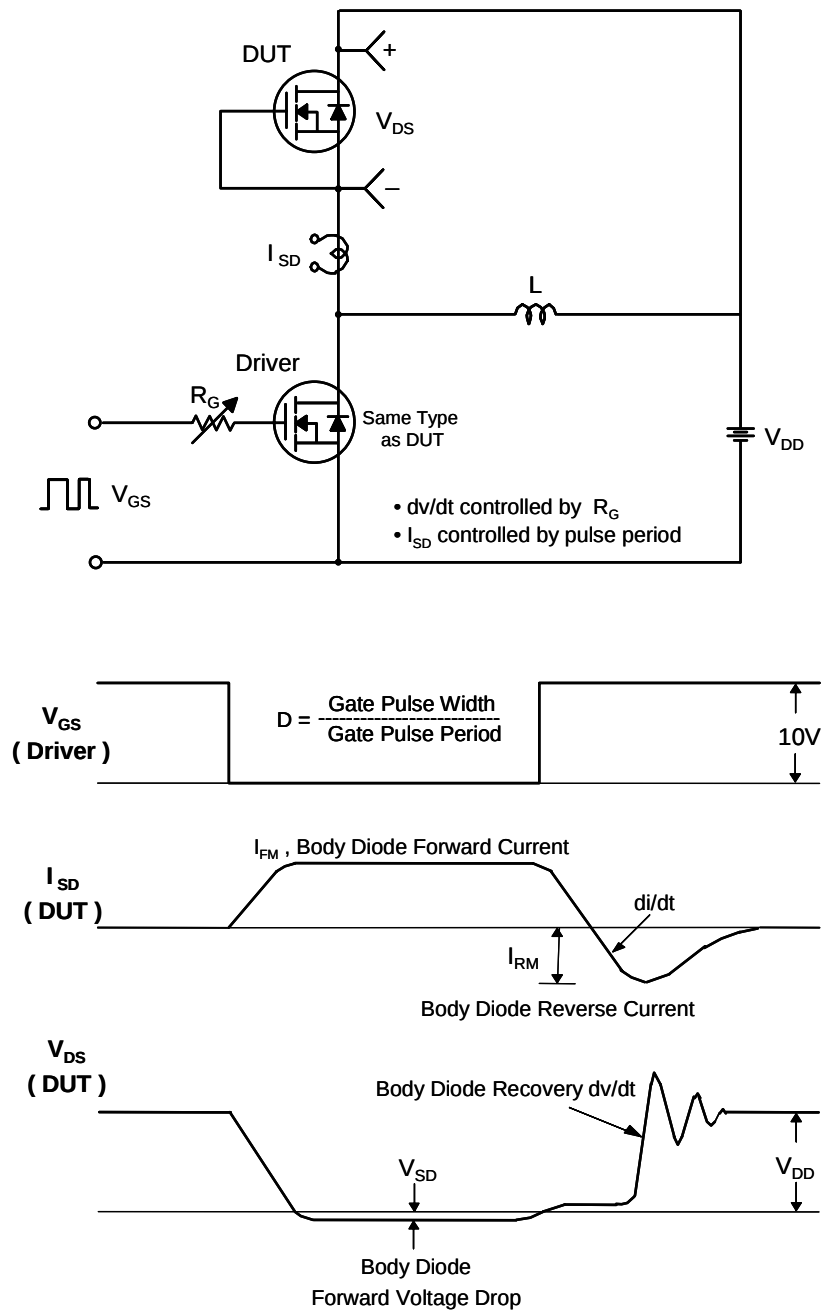


Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching Test Circuit & Waveforms

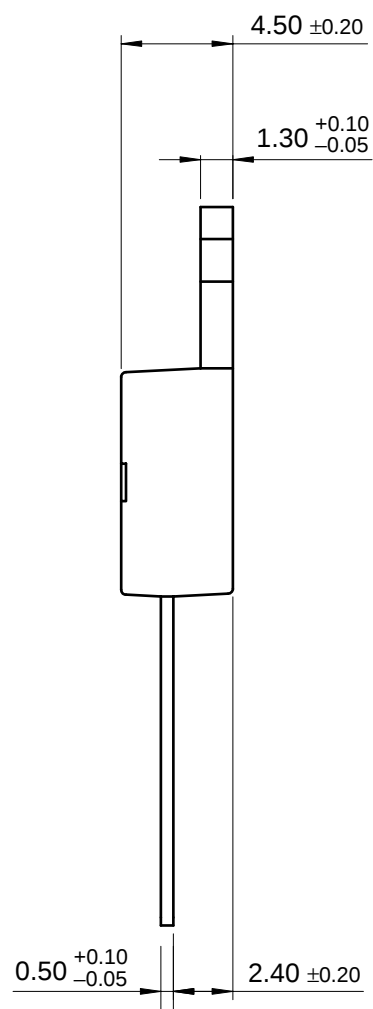


Peak Diode Recovery dv/dt Test Circuit & Waveforms

Technical drawing of a 3-pin connector. The drawing shows a top view and a side view. The top view is a rectangle with a central circular hole and two smaller circular holes on the left side. The side view shows the profile of the connector with three pins. Dimensions are given in millimeters (mm) with tolerances.

Dimensions (mm):

- Overall width: 9.90 ± 0.20
- Width of central hole: (8.70)
- Width of left holes: $\phi 3.60 \pm 0.10$
- Overall height: 13.08 ± 0.20
- Height of top section: (1.70)
- Height of middle section: 1.30 ± 0.10
- Height of bottom section: (1.46)
- Height of top flange: 2.80 ± 0.10
- Height of middle section: (3.70)
- Height of bottom section: (3.00)
- Height of bottom flange: 15.90 ± 0.20
- Maximum height: 18.95 MAX.
- Pin width: 1.27 ± 0.10
- Pin width: 1.52 ± 0.10
- Pin width: 0.80 ± 0.10
- Pin length: 10.08 ± 0.30
- Pin angle: (45°)
- Pin pitch: 2.54 TYP
- Pin pitch tolerance: $[2.54 \pm 0.20]$



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